AMENDMENTS TO THE SPECIFICATION:

Please amend the paragraphs beginning on page 16, line 10 and ending on page 16, line 23 of the specification as follows:

In the case of using an organic substrate as substrate 1, conductive pattern 2 of which surface layer includes Ag has been formed in advance by the photolithography method on the organic substrate, and Ni-plated layer having 1μm thickness is formed on that surface layer by the electroless plating method, so that a metal film [[5]] is obtained.

Next, the metal film [[5]] undergoes an oxidation treatment. Use of an organic substrate is regulated by an upper limit of a heating temperature, so that the oxidation treatment is preferably carried out in the following way: Prepare acid solution of not higher than pH3, and dip substrate 1 into the solution, or place substrate 1 together with the solution in an airtight space for oxidizing substrate 1. Such a chemical treatment oxidizes Ni to NiO. Metal oxide layer 3 thus obtained is thin and has a uniform distribution of film thickness, so that it can be formed uniformly at minute sections of conductive pattern 2.